

ECG[®] Semiconductors

ECG816, ECG817 RF/IF Amplifier

Features

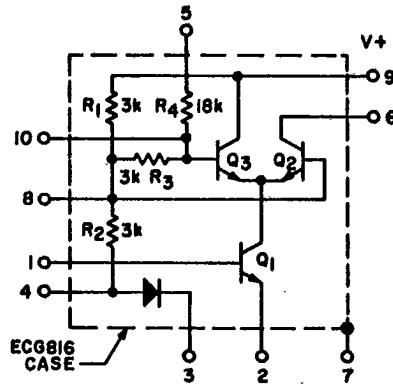
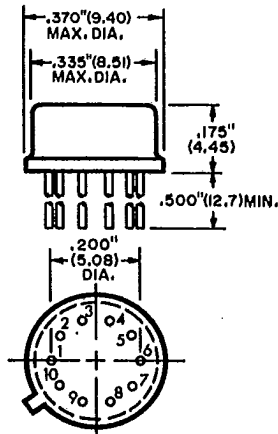
- Constant input impedance over entire AGC range
- High power gain
- Good noise figures
- Versatile applications

The ECG816 and ECG817 are silicon monolithic integrated circuits designed for communications applications as a RF/IF amplifier.

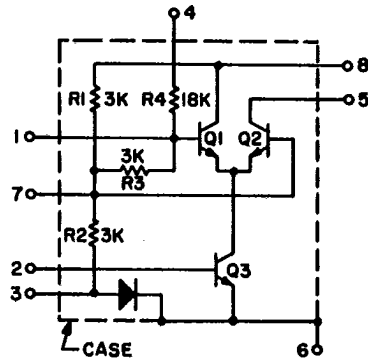
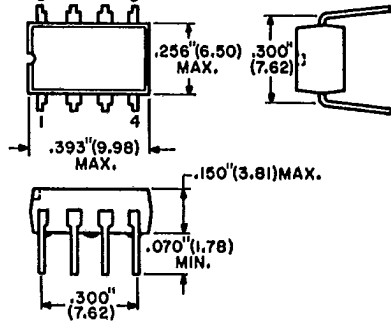
Pin Connections

| ECG816 | Symbol | ECG817 |
|--------|-----------------|--------|
| 1 | Sig In | 2 |
| 2 | GND | No Pin |
| 3 | GND | No Pin |
| 4 | Bypass | 3 |
| 5 | AGC | 4 |
| 6 | Output | 5 |
| 7 | GND | 6 |
| 8 | Bypass | 7 |
| 9 | V _{cc} | 8 |
| 10 | Bypass | 1 |

ECG816



ECG817



T-74-09-01

Note: All Pin Numbers Used in Tables and Circuits are for ECG816

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|-----------|--------------|----------------------------|
| Power Supply Voltage, Pin 9 | V_{CC} | 20 | Vdc |
| AGC Supply Voltage | V_{AGC} | 20 | Vdc |
| Input Differential Voltage, Pin 1 to Pin 4 ($R_S = 500 \Omega$) | V_{ID} | ± 5.0 | V(RMS) |
| Power Dissipation (Package Limitation) Metal Can Derate above $T_S = +25^\circ\text{C}$ | P_D | 680 4.6 | mW mW/ $^\circ\text{C}$ |
| Operating Ambient Temperature Range | T_{opg} | -155 to +125 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | -65 to +150 | $^\circ\text{C}$ |

Electrical Characteristics ($V_{CC} = +6 \text{ Vdc}$, $T_A = +25^\circ\text{C}$)

| Characteristic | Conditions | Figure | Symbol | Min | Typ | Max | Unit |
|-------------------------------------|---|--------|-----------|--------------|----------|--------------|------|
| DC Characteristics | | | | | | | |
| Output Voltage | $V_{AGC} = 0 \text{ Vdc}$ $V_{AGC} = +6 \text{ Vdc}$ | 1 | V_O | 3.80 5.90 | -- | 4.65 6.00 | Vdc |
| Test Voltage | $V_{AGC} = 0 \text{ Vdc}$ $V_{AGC} = +6 \text{ Vdc}$ | 1 | V_B | 2.85 3.25 | -- | 3.40 3.80 | Vdc |
| Supply Drain Current | $V_{AGC} = 0 \text{ Vdc}$ $V_{AGC} = +6 \text{ Vdc}$ | 1 | I_D | -- | -- | 2.2 2.5 | mAdc |
| AGC Supply Drain Current | $V_{AGC} = 0 \text{ Vdc}$ $V_{AGC} = +6 \text{ Vdc}$ | 1 | I_{AGC} | -- | -- | -0.2 0.18 | mAdc |
| Small-Signal Characteristics | | | | | | | |
| Small-Signal Voltage Gain | $f = 500 \text{ MHz}$ | 2 | A_V | 22 | -- | 29 | dB |
| Bandwidth | -30 dB | 2 | BW | 22 | -- | -- | MHz |
| Transducer Power Gain | $f = 60 \text{ MHz}$, BW = 6 MHz $f = 100 \text{ MHz}$, BW = 6 MHz | 3 | A_p | -- | 25 21 | -- | dB |

Typical Characteristics ($V_{CC} = 6.0 \text{ Vdc}$, $T_A = +25^\circ\text{C}$ unless otherwise noted.)

FIGURE 1 - DC CHARACTERISTICS TEST CIRCUIT

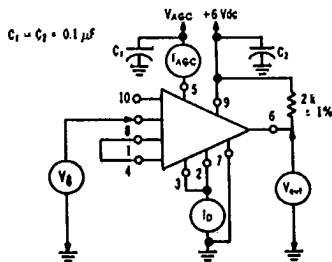
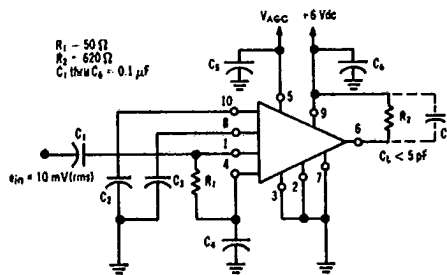


FIGURE 2 - VOLTAGE GAIN AND BANDWIDTH TEST CIRCUIT



ECG816, ECG817

38

FIGURE 3 - POWER GAIN TEST CIRCUIT @ 60 MHz

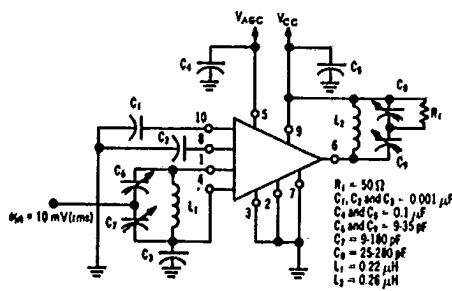


FIGURE 4 - DRAIN CURRENT TEMPERATURE CHARACTERISTICS

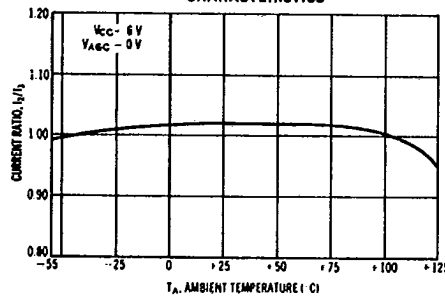


FIGURE 5 - INPUT RESISTANCE AND CAPACITANCE versus FREQUENCY

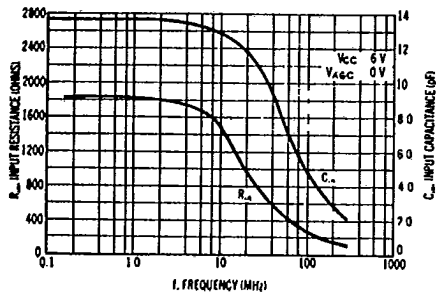


FIGURE 6 - INPUT RESISTANCE AND CAPACITANCE versus AGC VOLTAGE

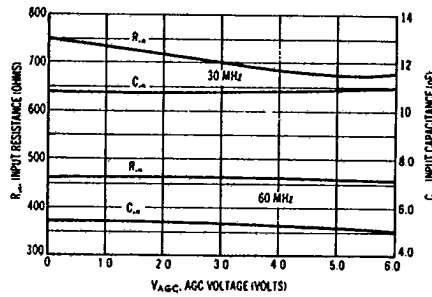


FIGURE 7 - OUTPUT RESISTANCE AND CAPACITANCE versus FREQUENCY

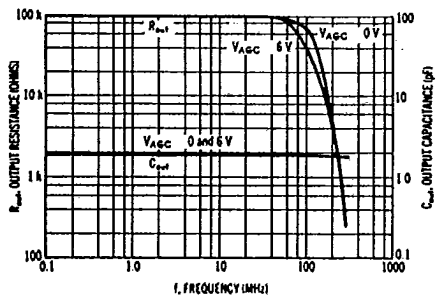


FIGURE 8 - OUTPUT RESISTANCE AND CAPACITANCE versus AGC VOLTAGE

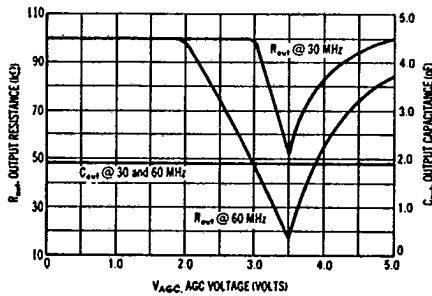


FIGURE 9 - MAXIMUM TRANSDUCER POWER GAIN versus FREQUENCY

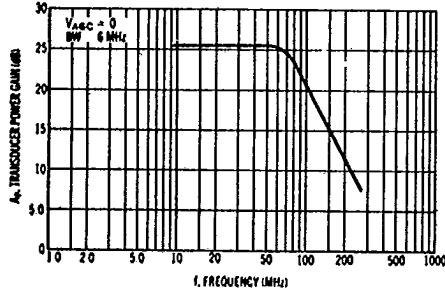
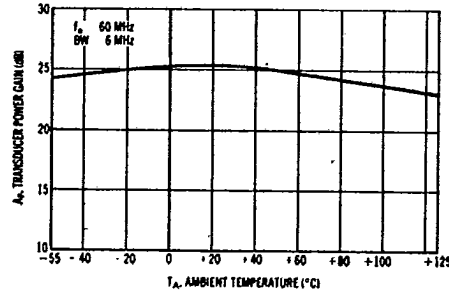


FIGURE 10 - TRANSDUCER POWER GAIN versus TEMPERATURE



T-74-09-01

FIGURE 11 - TRANSDUCER POWER BANDWIDTH versus AGC VOLTAGE

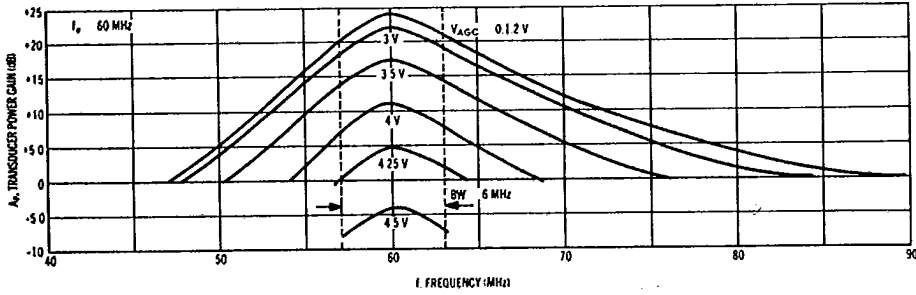


FIGURE 12 - NOISE FIGURE AND OPTIMUM SOURCE RESISTANCE versus FREQUENCY

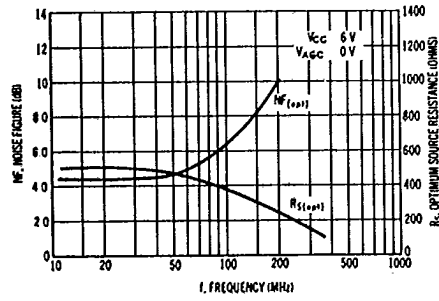


FIGURE 13 - NOISE FIGURE versus SOURCE RESISTANCE

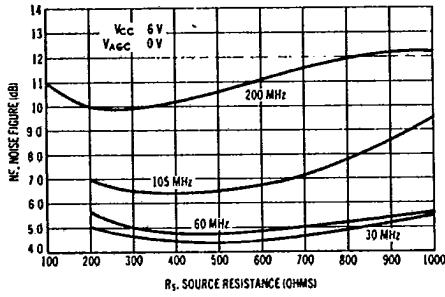


FIGURE 14 - y_{21} , FORWARD-TRANSFER ADMITTANCE versus FREQUENCY

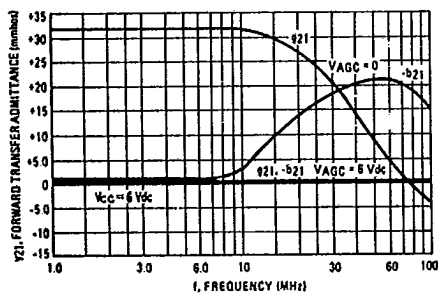


FIGURE 15 - y_{21} , FORWARD-TRANSFER ADMITTANCE versus AGC VOLTAGE

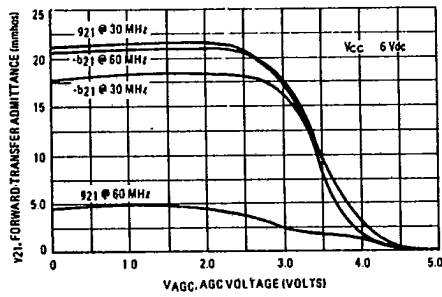


FIGURE 16 - y_{12} , REVERSE-TRANSFER-ADMITTANCE versus FREQUENCY

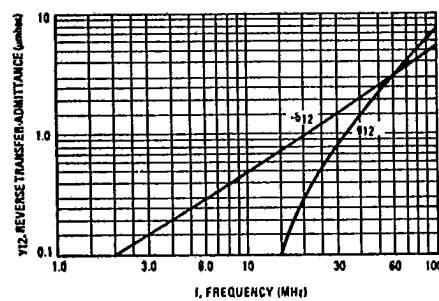
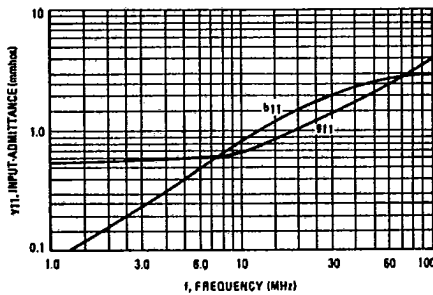


FIGURE 17 - y_{11} , INPUT-ADMITTANCE versus FREQUENCY



The γ_{12} shown in Figure 16 illustrates the extremely low feedback with no contribution from the external mounting circuitry. However, in many cases the external circuitry may contribute as much or more to the total feedback than the ECG816 or ECG817 does.

To perform more accurate design calculations of gain, stability, and input - output impedances it is recommended that the designer first determine the total feedback of device plus circuitry.

This can be done in one of two ways:

1. Measure the total γ_{12} or s_{12} of the device installed in its mounting circuitry, or
2. Measure the γ_{12} of the circuitry alone (without the device installed) and add the circuit γ_{12} to the γ_{12} for the device given in Figure 16.

T-74-09-01

FIGURE 18 - γ_{22} , OUTPUT ADMITTANCE versus FREQUENCY

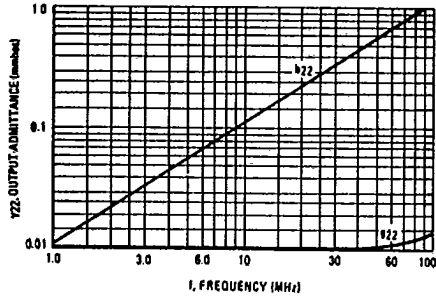


FIGURE 19 - s_{11} AND s_{22} , INPUT AND OUTPUT REFLECTION COEFFICIENT

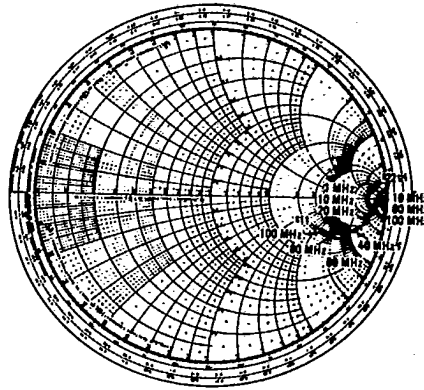


FIGURE 20 - s_{11} , INPUT REFLECTION COEFFICIENT versus FREQUENCY

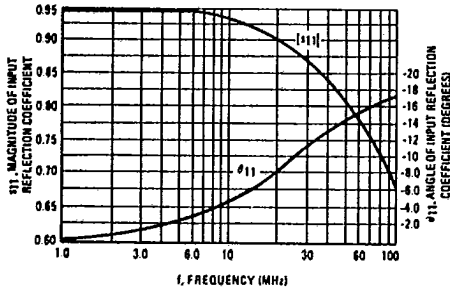
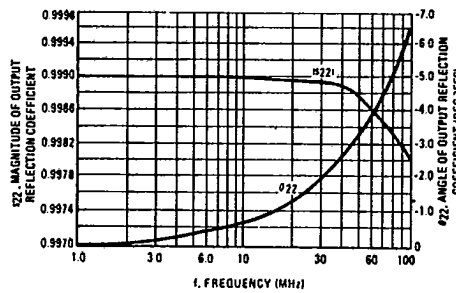


FIGURE 21 - s_{22} , OUTPUT REFLECTION COEFFICIENT versus FREQUENCY



T-74-09-01

FIGURE 22 - 421, FORWARD TRANSMISSION COEFFICIENT (GAIN)

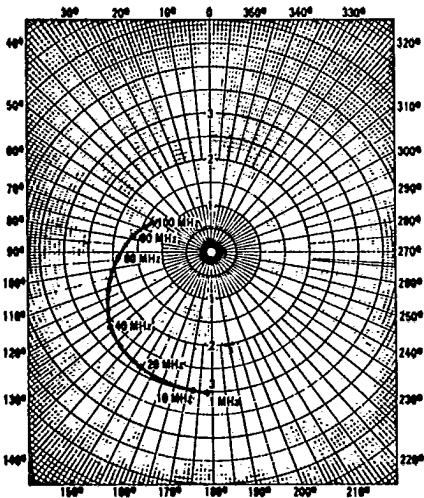


FIGURE 23 - 412, REVERSE TRANSMISSION COEFFICIENT (FEEDBACK)

